

# BF909; BF909R

N-channel dual gate MOS-FETs

Rev. 02 — 19 November 2007

Product data sheet

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# N-channel dual gate MOS-FETs

# BF909; BF909R

## FEATURES

- Specially designed for use at 5 V supply voltage
- High forward transfer admittance
- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Superior cross-modulation performance during AGC.

## APPLICATIONS

- VHF and UHF applications with 3 to 7 V supply voltage such as television tuners and professional communications equipment.

## DESCRIPTION

Enhancement type field-effect transistor in a plastic microminiature SOT143 or SOT143R package. The

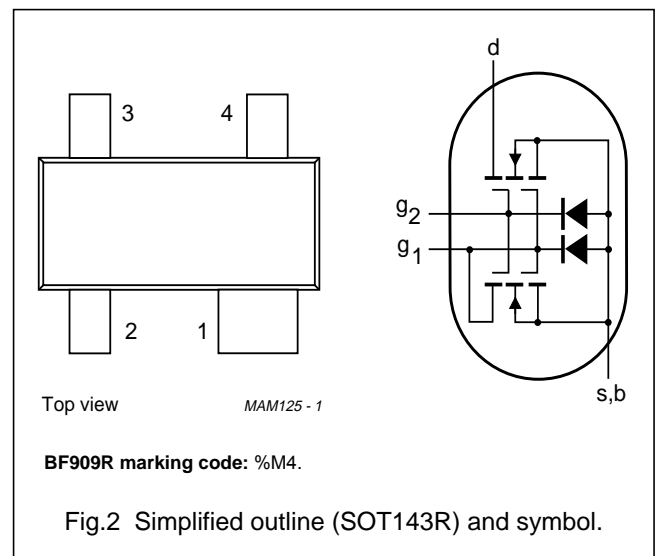
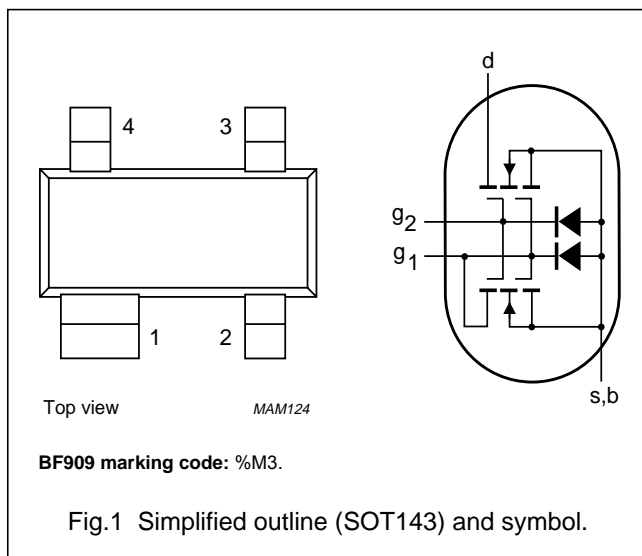
transistor consists of an amplifier MOS-FET with source and substrate interconnected and an internal bias circuit to ensure good cross-modulation performance during AGC.

### CAUTION

The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

## PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g <sub>2</sub>	gate 2
4	g <sub>1</sub>	gate 1



## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage		–	–	7	V
I <sub>D</sub>	drain current		–	–	40	mA
P <sub>tot</sub>	total power dissipation		–	–	200	mW
T <sub>j</sub>	operating junction temperature		–	–	150	°C
y <sub>fs</sub>	forward transfer admittance		36	43	50	mS
C <sub>ig1-s</sub>	input capacitance at gate 1		–	3.6	4.3	pF
C <sub>rs</sub>	reverse transfer capacitance	f = 1 MHz	–	35	50	fF
F	noise figure	f = 800 MHz	–	2	2.8	dB

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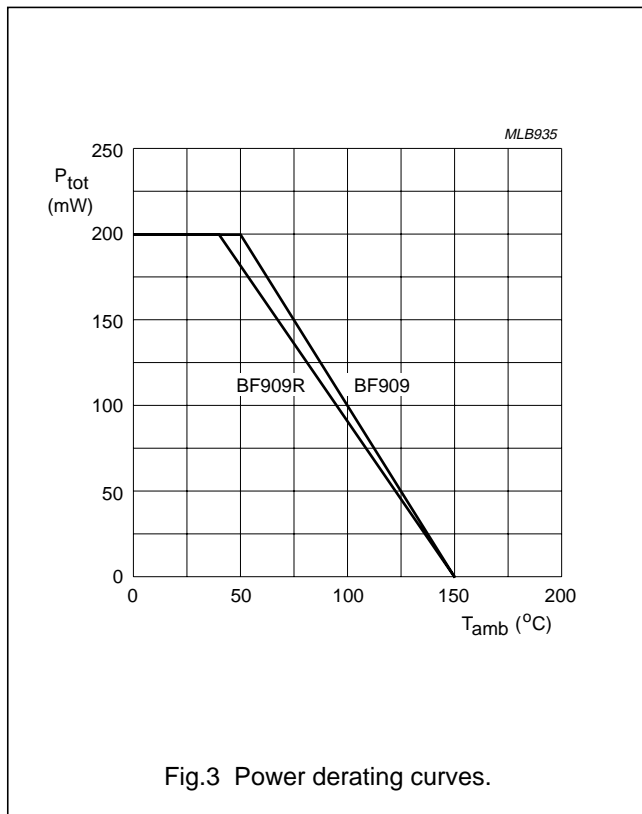
**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DS}$	drain-source voltage		–	7	V
$I_D$	drain current		–	40	mA
$I_{G1}$	gate 1 current		–	$\pm 10$	mA
$I_{G2}$	gate 2 current		–	$\pm 10$	mA
$P_{tot}$	total power dissipation BF909 BF909R	see Fig.3 up to $T_{amb} = 50\text{ }^\circ\text{C}$ ; note 1 up to $T_{amb} = 40\text{ }^\circ\text{C}$ ; note 1	– –	200 200	mW mW
$T_{stg}$	storage temperature		–65	+150	$^\circ\text{C}$
$T_j$	operating junction temperature		–	150	$^\circ\text{C}$

**Note**

1. Device mounted on a printed-circuit board.



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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1		
	BF909		500	K/W
	BF909R		550	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point	note 2		
	BF909	$T_s = 92\text{ °C}$	290	K/W
	BF909R	$T_s = 78\text{ °C}$	360	K/W

## Notes

1. Device mounted on a printed-circuit board.
2.  $T_s$  is the temperature at the soldering point of the source lead.

## STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$ ; $I_{G1-S} = 10\text{ mA}$	6	15	V
$V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$ ; $I_{G2-S} = 10\text{ mA}$	6	15	V
$V_{(F)S-G1}$	forward source-gate 1 voltage	$V_{G2-S} = V_{DS} = 0$ ; $I_{S-G1} = 10\text{ mA}$	0.5	1.5	V
$V_{(F)S-G2}$	forward source-gate 2 voltage	$V_{G1-S} = V_{DS} = 0$ ; $I_{S-G2} = 10\text{ mA}$	0.5	1.5	V
$V_{G1-S(th)}$	gate 1-source threshold voltage	$V_{G2-S} = 4\text{ V}$ ; $V_{DS} = 5\text{ V}$ ; $I_D = 20\text{ }\mu\text{A}$	0.3	1	V
$V_{G2-S(th)}$	gate 2-source threshold voltage	$V_{G1-S} = V_{DS} = 5\text{ V}$ ; $I_D = 20\text{ }\mu\text{A}$	0.3	1.2	V
$I_{DSX}$	drain-source current	$V_{G2-S} = 4\text{ V}$ ; $V_{DS} = 5\text{ V}$ ; $R_{G1} = 120\text{ k}\Omega$ ; note 1	12	20	mA
$I_{G1-SS}$	gate 1 cut-off current	$V_{G1-S} = 5\text{ V}$ ; $V_{G2-S} = V_{DS} = 0$	–	50	nA
$I_{G2-SS}$	gate 2 cut-off current	$V_{G2-S} = 5\text{ V}$ ; $V_{G1-S} = V_{DS} = 0$	–	50	nA

## Note

1.  $R_{G1}$  connects gate 1 to  $V_{GG} = 5\text{ V}$ ; see Fig.18.

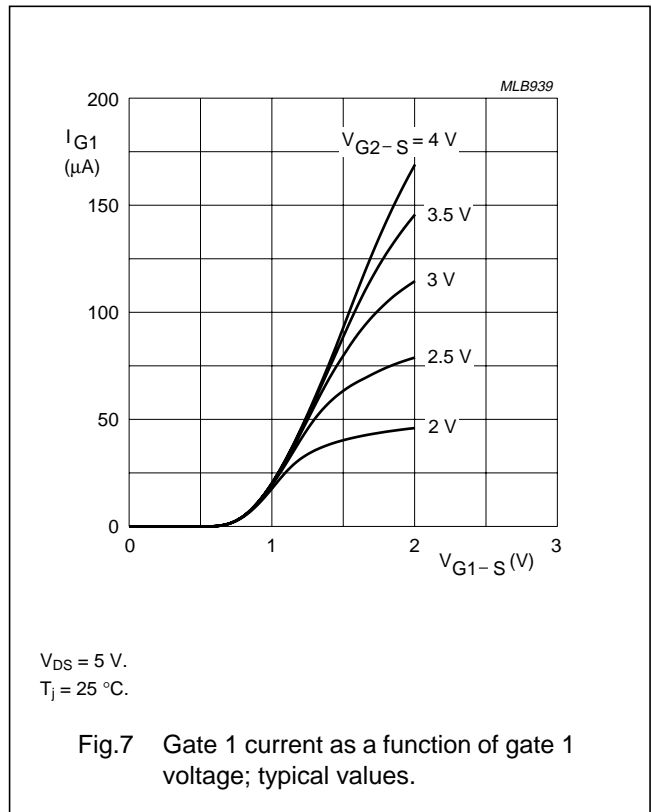
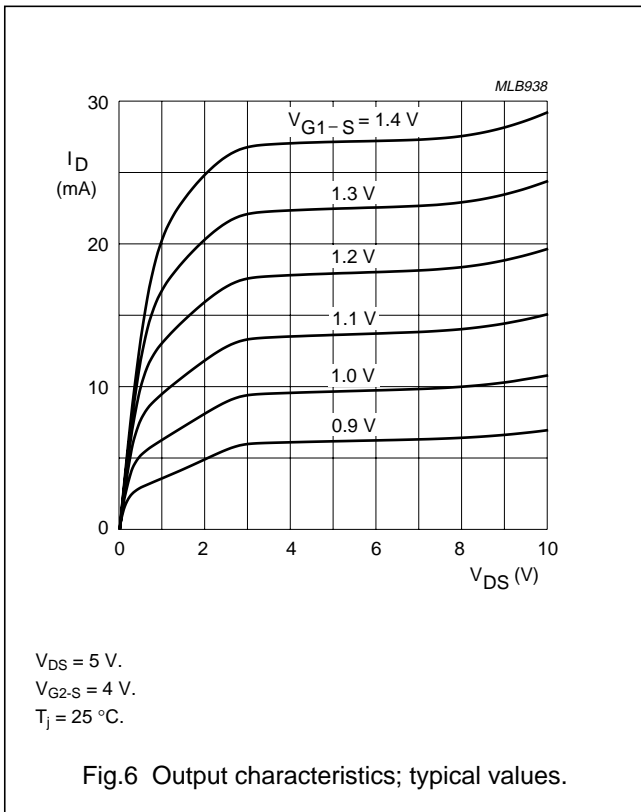
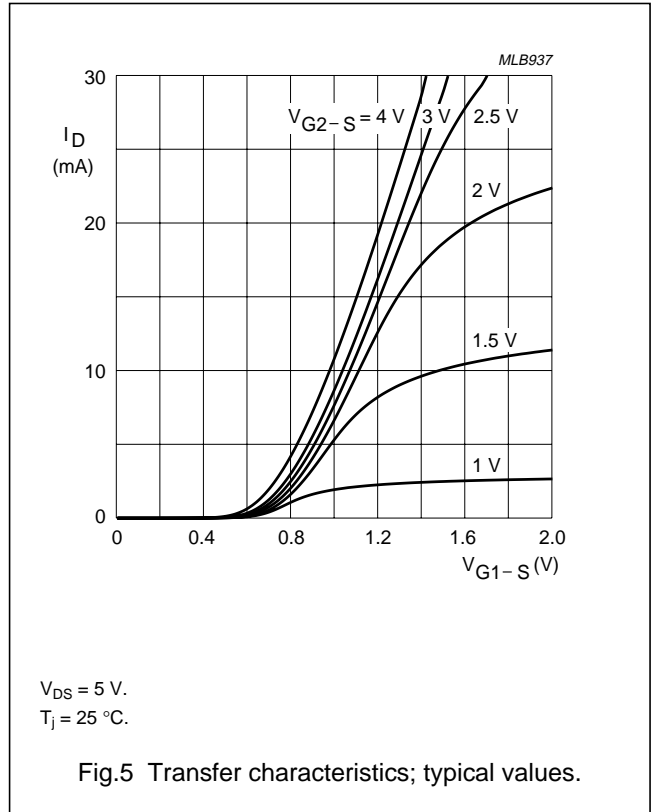
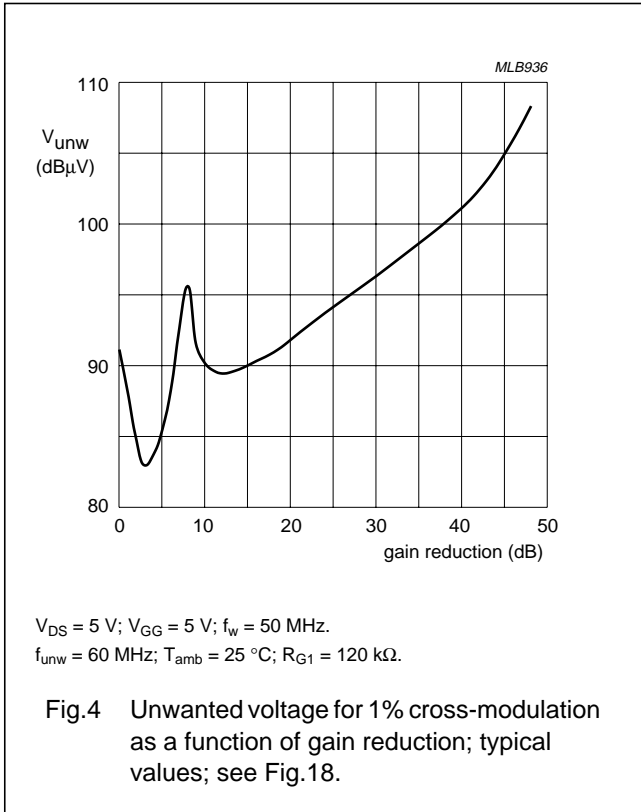
## DYNAMIC CHARACTERISTICS

Common source;  $T_{amb} = 25\text{ °C}$ ;  $V_{DS} = 5\text{ V}$ ;  $V_{G2-S} = 4\text{ V}$ ;  $I_D = 15\text{ mA}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ y_{fs} $	forward transfer admittance	pulsed; $T_j = 25\text{ °C}$	36	43	50	mS
$C_{ig1-s}$	input capacitance at gate 1	$f = 1\text{ MHz}$	–	3.6	4.3	pF
$C_{ig2-s}$	input capacitance at gate 2	$f = 1\text{ MHz}$	–	2.3	3	pF
$C_{os}$	drain-source capacitance	$f = 1\text{ MHz}$	–	2.3	3	pF
$C_{rs}$	reverse transfer capacitance	$f = 1\text{ MHz}$	–	35	50	fF
F	noise figure	$f = 800\text{ MHz}$ ; $G_S = G_{Sopt}$ ; $B_S = B_{Sopt}$	–	2	2.8	dB

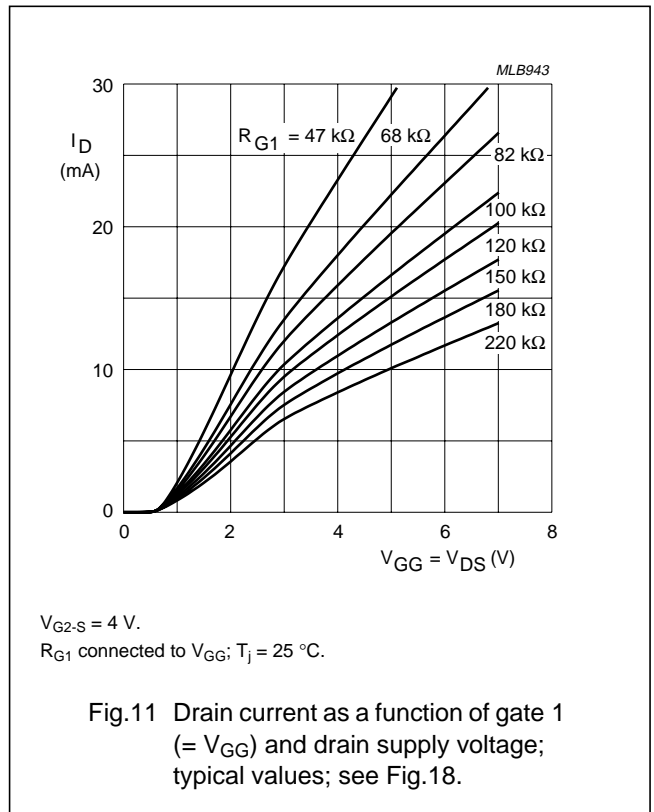
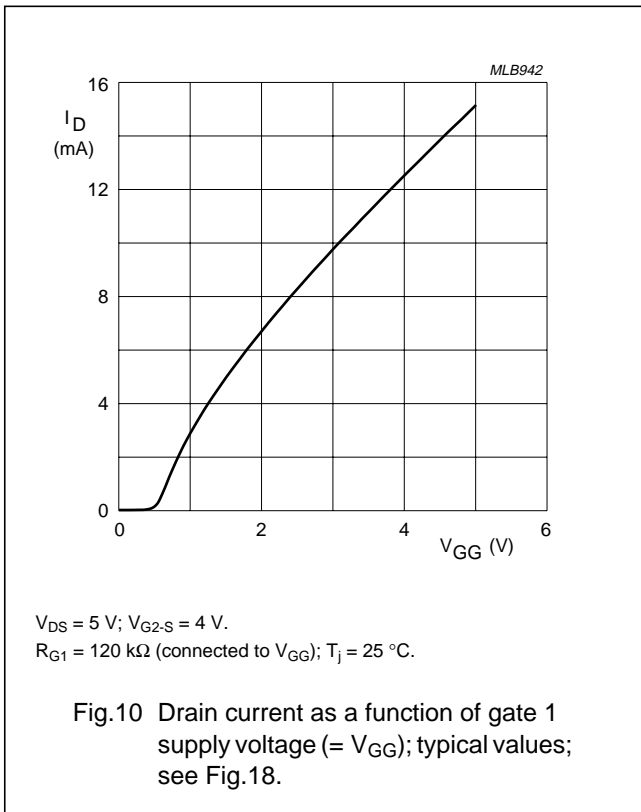
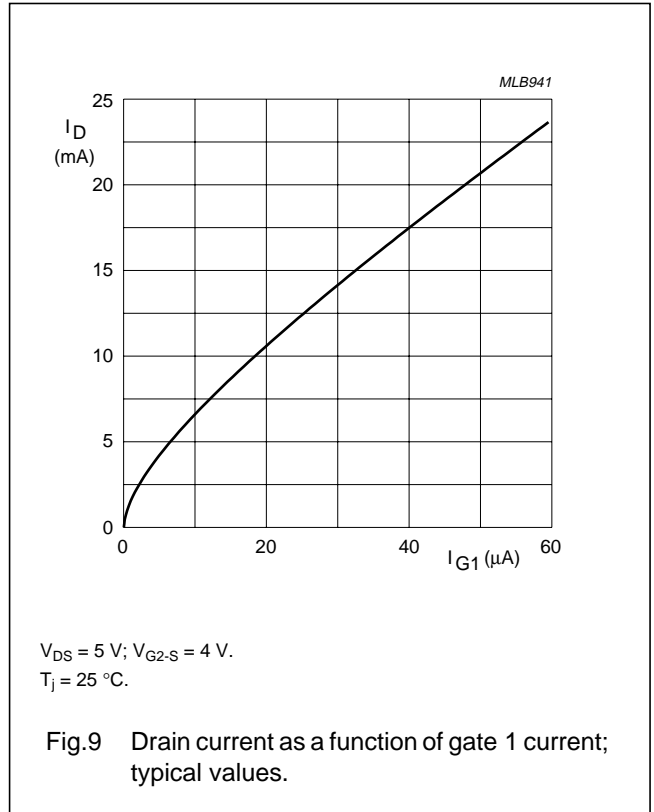
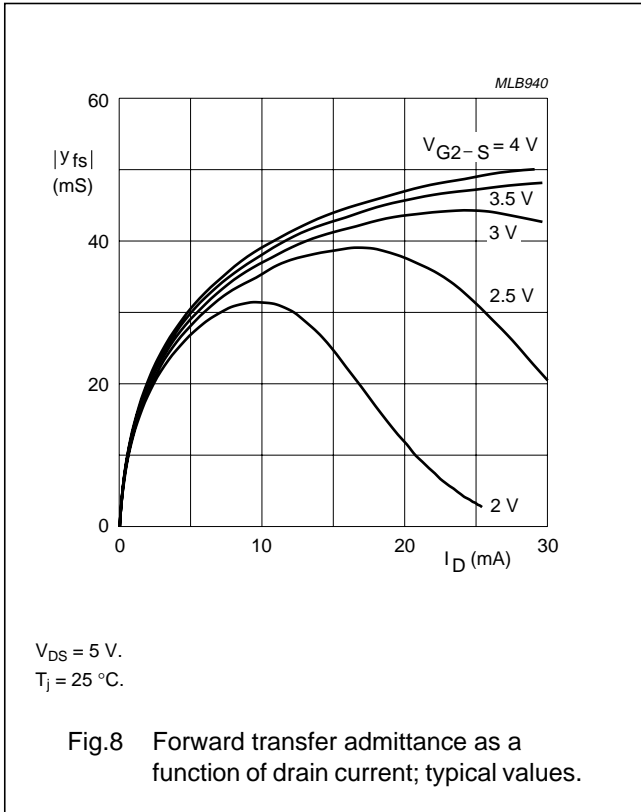
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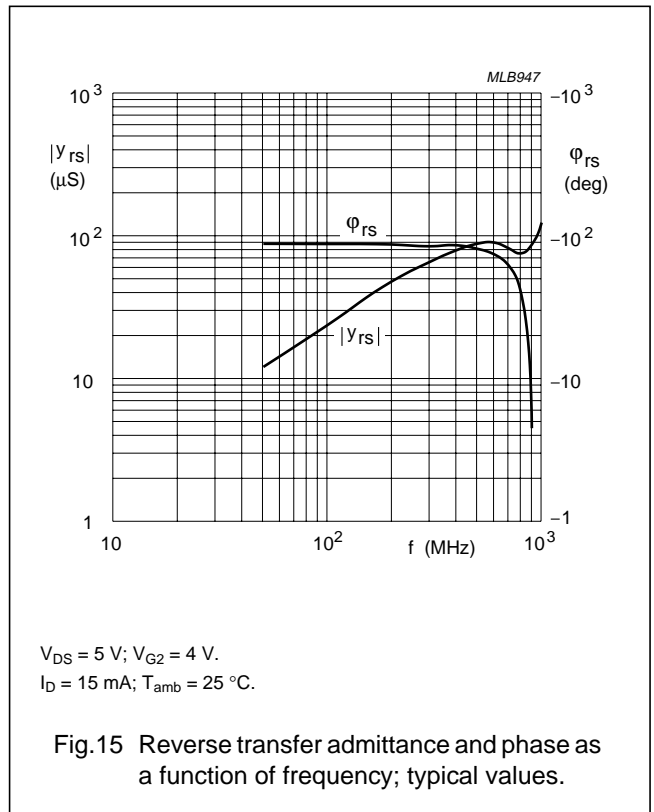
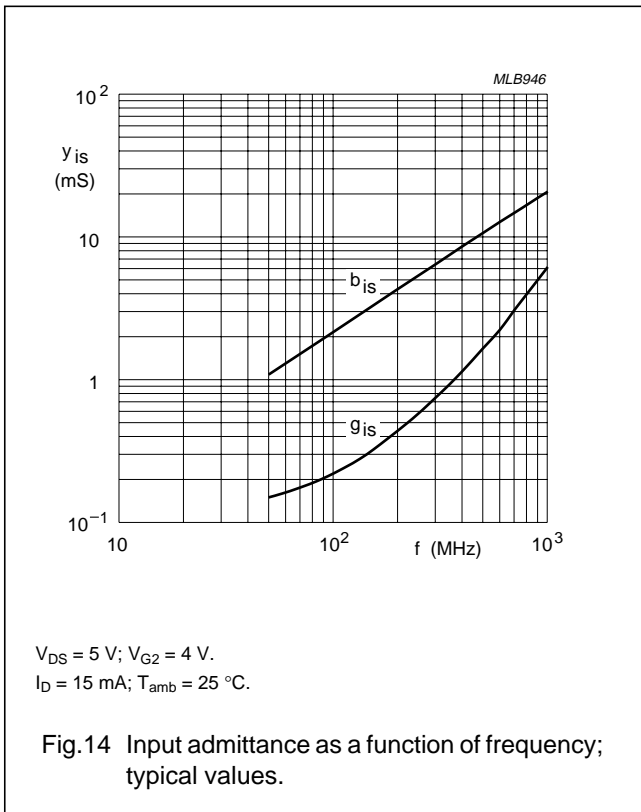
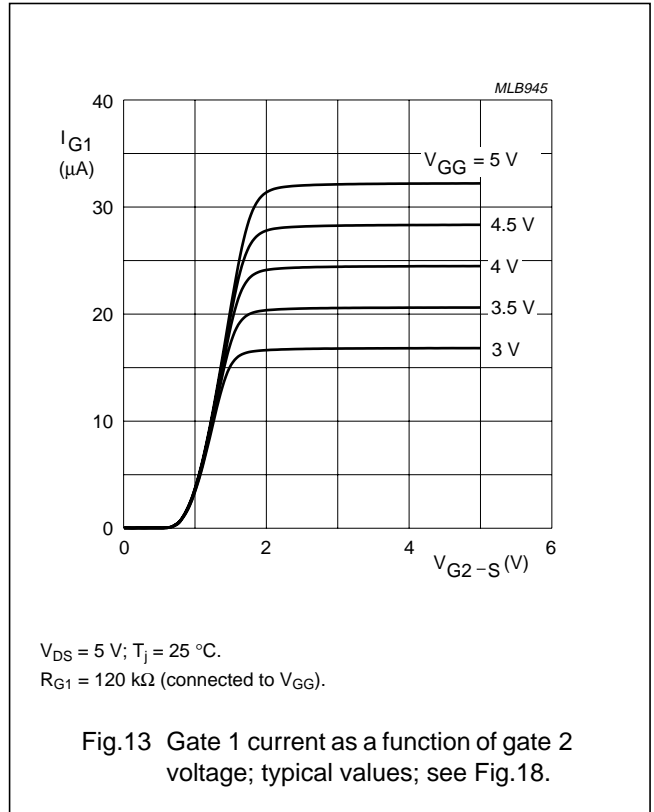
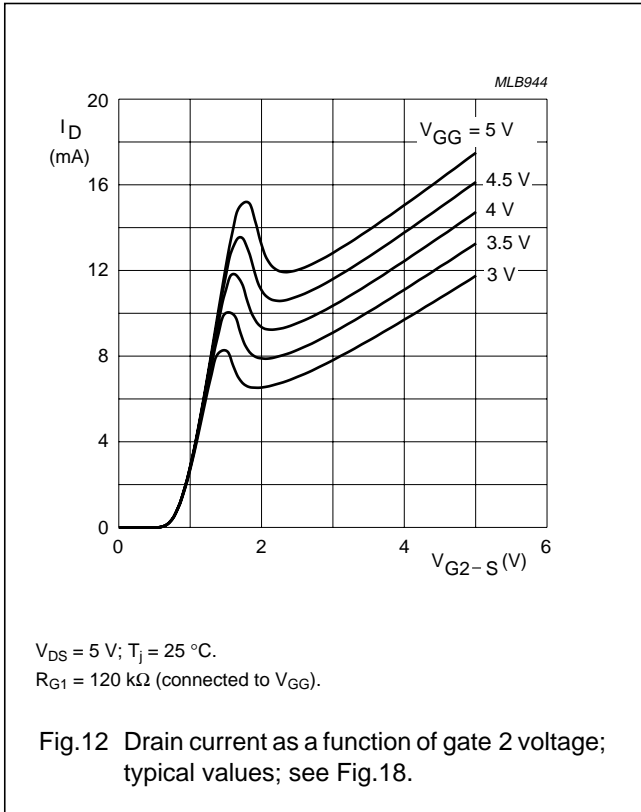
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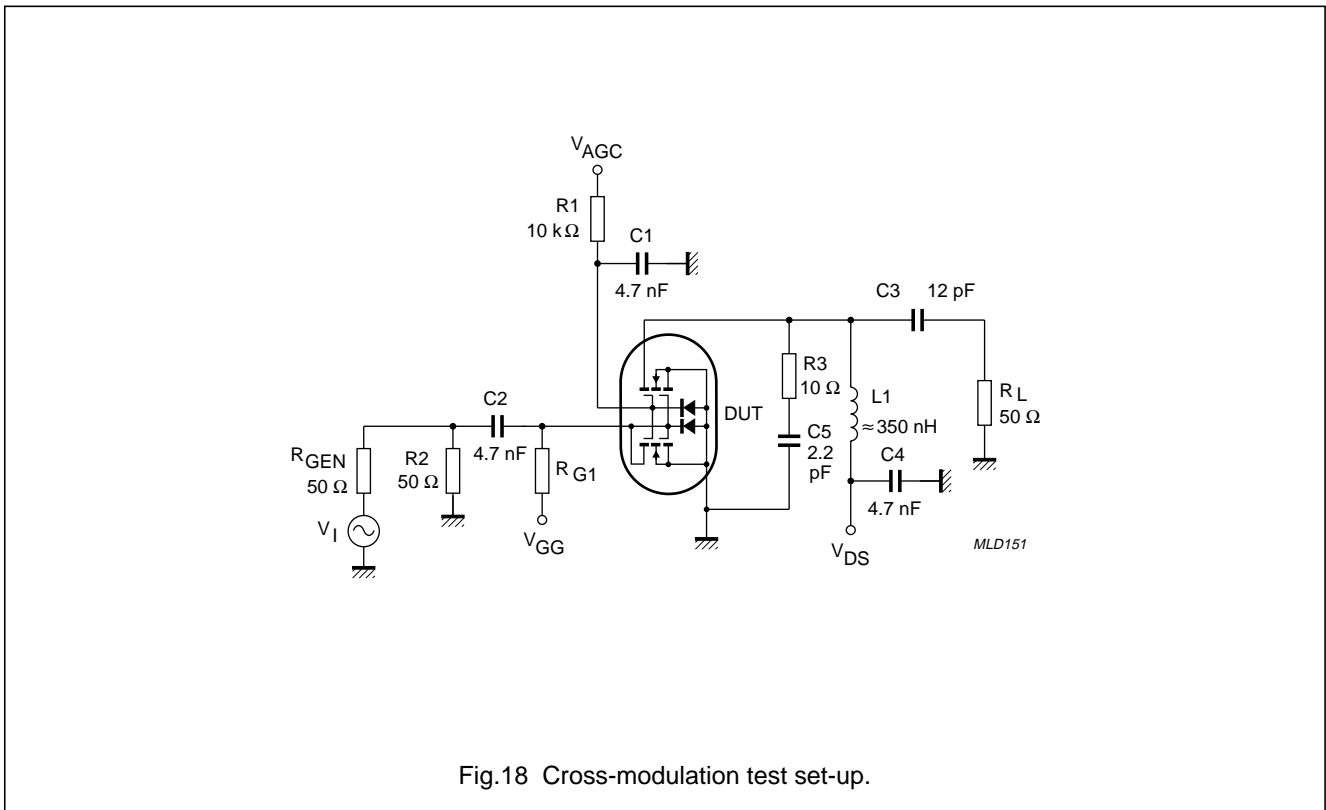
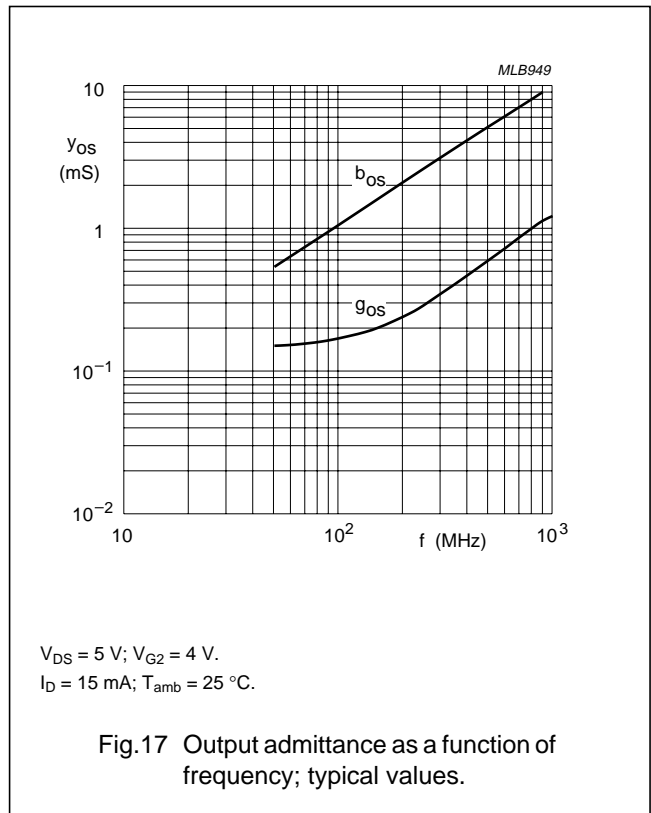
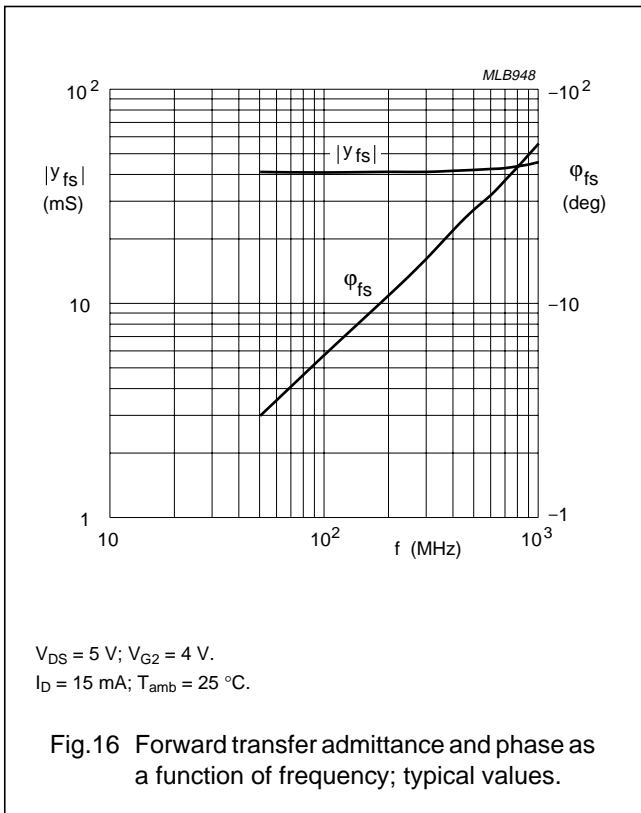
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**Table 1** Scattering parameters:  $T_{amb} = 25\text{ °C}$ ;  $V_{DS} = 5\text{ V}$ ;  $V_{G2-S} = 4\text{ V}$ ;  $I_D = 15\text{ mA}$ 

f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.985	-6.4	4.064	172.3	0.001	86.9	0.985	-3.2
100	0.978	-12.6	3.997	164.9	0.002	82.7	0.982	-6.4
200	0.957	-25.0	3.886	150.8	0.005	74.3	0.973	-12.6
300	0.931	-36.5	3.682	137.3	0.006	68.9	0.960	-18.6
400	0.899	-47.6	3.484	123.8	0.007	59.6	0.947	-24.2
500	0.868	-57.4	3.260	111.7	0.007	57.9	0.936	-29.6
600	0.848	-66.6	3.053	101.0	0.006	58.5	0.927	-34.8
700	0.816	-74.6	2.829	90.3	0.005	65.5	0.919	-39.8
800	0.792	-82.2	2.652	79.9	0.005	83.3	0.913	-44.6
900	0.772	-89.3	2.470	69.5	0.005	114.9	0.910	-49.5
1000	0.754	-95.6	2.328	59.5	0.006	138.7	0.909	-54.6

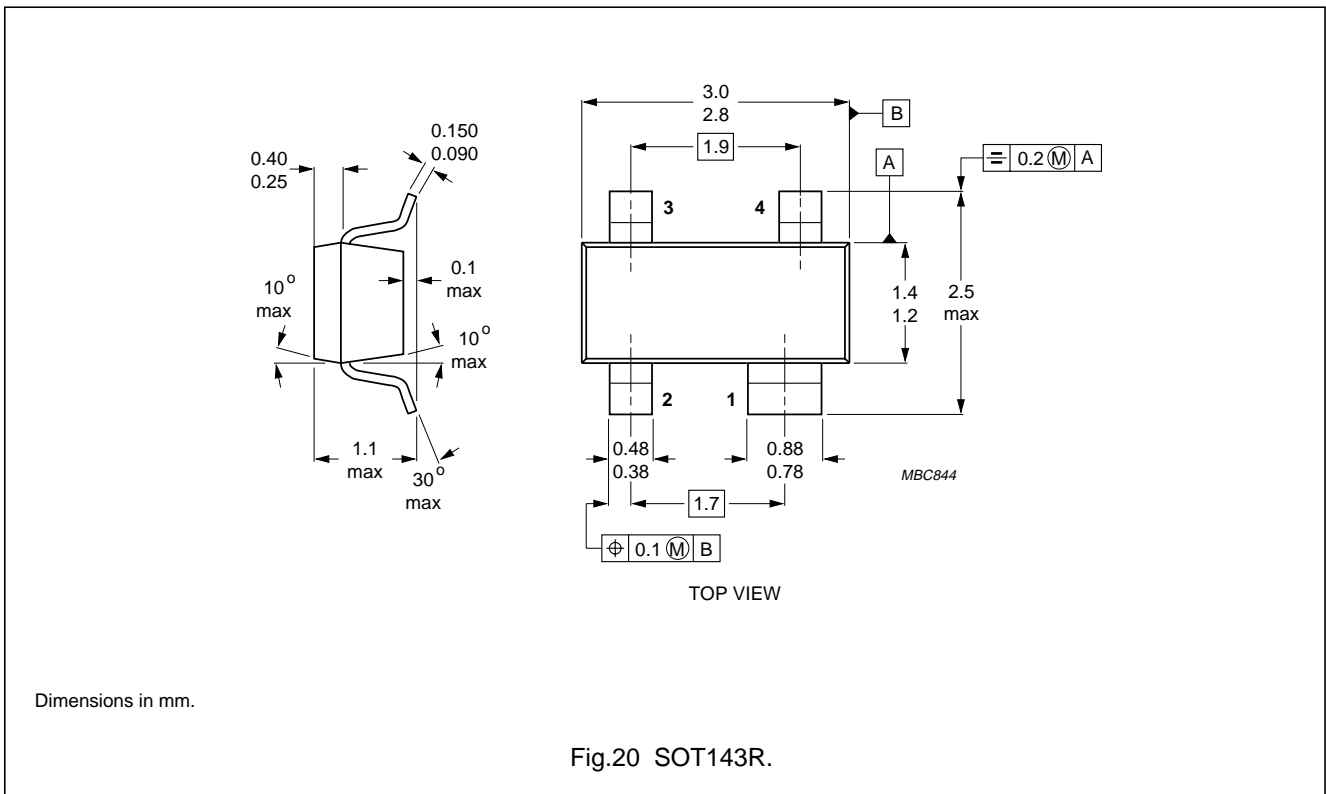
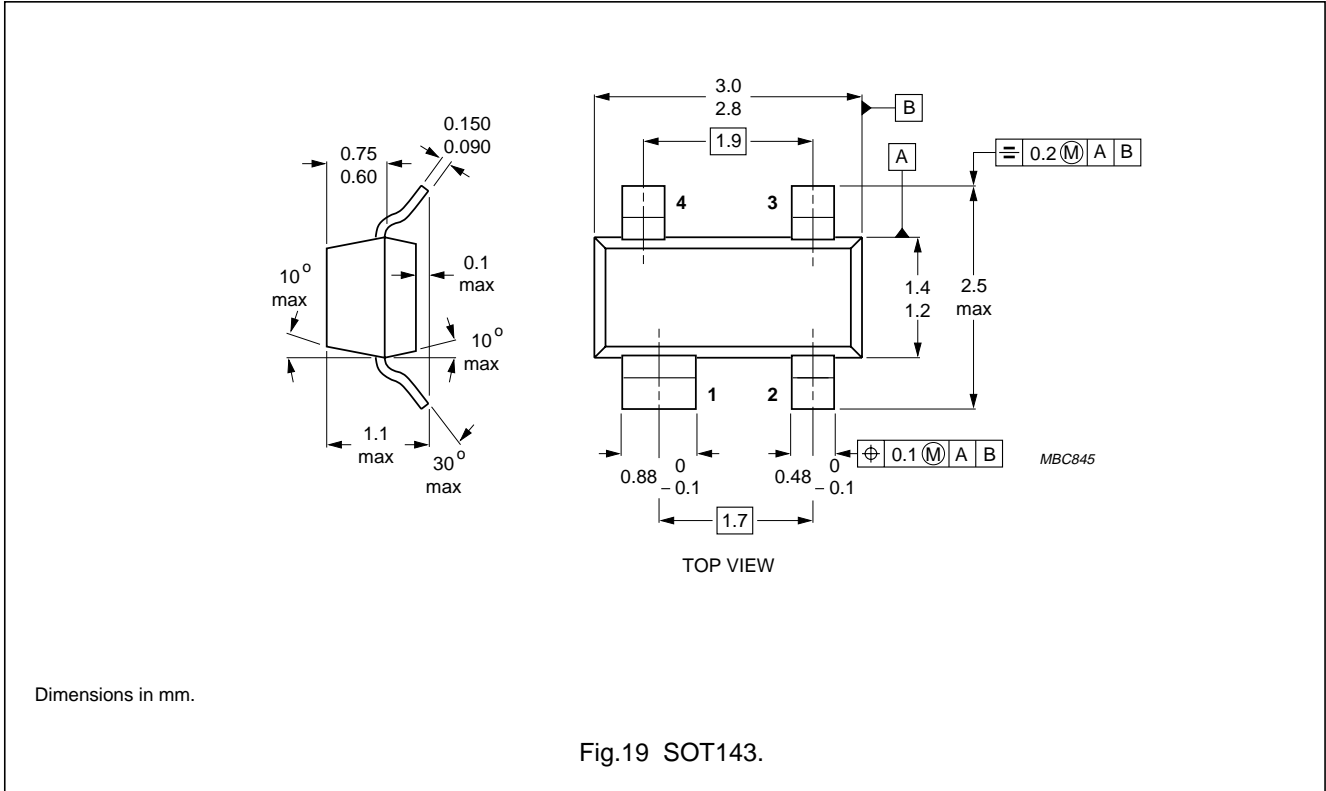
**Table 2** Noise data:  $T_{amb} = 25\text{ °C}$ ;  $V_{DS} = 5\text{ V}$ ;  $V_{G2-S} = 4\text{ V}$ ;  $I_D = 15\text{ mA}$ 

f (MHz)	F <sub>min</sub> (dB)	Γ <sub>opt</sub>		r <sub>n</sub>
		(ratio)	(deg)	
800	2.00	0.603	67.71	0.581

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PACKAGE OUTLINES



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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## Revision history

### Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF909_N_2	20071119	Product data sheet	-	BF909_1
Modifications:	• Fig.1 and 2 on page 2; Figure note changed			
BF909_1	19950425	Product specification	-	-

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